P.T.O.

## B.Tech. BTCSVI / BTECVI / BTELVI

## **Term-End Examination**

00634

**BIEL-001** 

June, 2014

## **BIEL-001: BASICS OF ELECTRONICS ENGINEERING**

Tin	ne : 3 i	hours Maximum Marks	Maximum Marks : 70	
<b>Note:</b> Attempt any <b>seven</b> questions. Each question carriequal marks.				
1.	(a)	How do energy levels in an atom transform to energy bands in a solid?	5	
	(b)	How can you differentiate solids on the basis of energy band diagram?	5	
2.	(a) (b)	What is Fermi-level? Draw the Fermi- energy band-diagram for conductors, semiconductors and metals. Derive the continuity equation.	5 5	
3.	und	Explain the working of a P-N junction diode under zero bias. Also explain the formation of barrier potential and depletion layer.		
4.	(a) (b)		<i>5</i>	
	(b)	-	L	

5.	(a)	and the Avalanche diodes.	5
	(b)	Explain the phenomenon of base-width Modulation/Early effect in transistors.	5
6.		acteristics of a BJT in common-emitter iguration and label the regions of operation	10
7.	(a)	Define $\alpha$ and $\beta$ for transistor and also derive the relation between them.	5
	(b)	Briefly explain the construction and working of a unijunction transistor (UJT).	5
8.	n-ch tran	ain the construction and working of an annel JFET. Also draw the output and the sfer characteristics. Briefly explain the ept of pinch-off.	10
9.	(a)	With neat circuit diagram briefly explain the working of a bridge-rectifier.	5
	(b)	A diode whose internal resistance is 20 $\Omega$ is to supply power to a 1 k $\Omega$ load from a 110 V (rms) source of supply.	
		Calculate:	
		(i) Peak load current	
		(ii) DC load current	
		(iii) Peak inverse voltage	5

- **10.** Write short notes on any **two** of the following:  $2\times 5=10$ 
  - (a) Varactor diode
  - (b) PIN diode
  - (c) Tunnel diode